

**FEATURES**

- **HIGH POWER**  
P1dB=39.5dBm at 13.75GHz to 14.5GHz
- **BROAD BAND INTERNALLY MATCHED FET**
- **HIGH GAIN**  
G1dB=5.5dB at 13.75GHz to 14.5GHz
- **HERMETICALLY SEALED PACKAGE**

**RF PERFORMANCE SPECIFICATIONS ( Ta= 25°C )**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 9V f= 13.75 to 14.5GHz	dBm	39.0	39.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	4.5	5.5	—
Drain Current	IDS1		A	—	4.0	5.0
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	18	—
3 <sup>rd</sup> Order Intermodulation Distortion	IM3	Two-Tone Test Po=29.0 dBm	dBc	-42	-45	—
Drain Current	IDS2	(Single Carrier Level)	A	—	4.0	5.0
Channel Temperature Rise	ΔTch	VDS X IDS X Rth(c-c)	°C	—	—	90

**Recommended gate resistance(Rg) : Rg= 100 Ω(MAX.)**

**ELECTRICAL CHARACTERISTICS ( Ta= 25°C )**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 4.8A	mS	—	2800	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 145mA	V	-2.0	-3.5	-5.0
Saturated Drain Current	IDSS	VDS= 3V VGS=0V	A	—	10.0	—
Gate-Source Breakdown Voltage	VGSO	IGS= -145μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.5

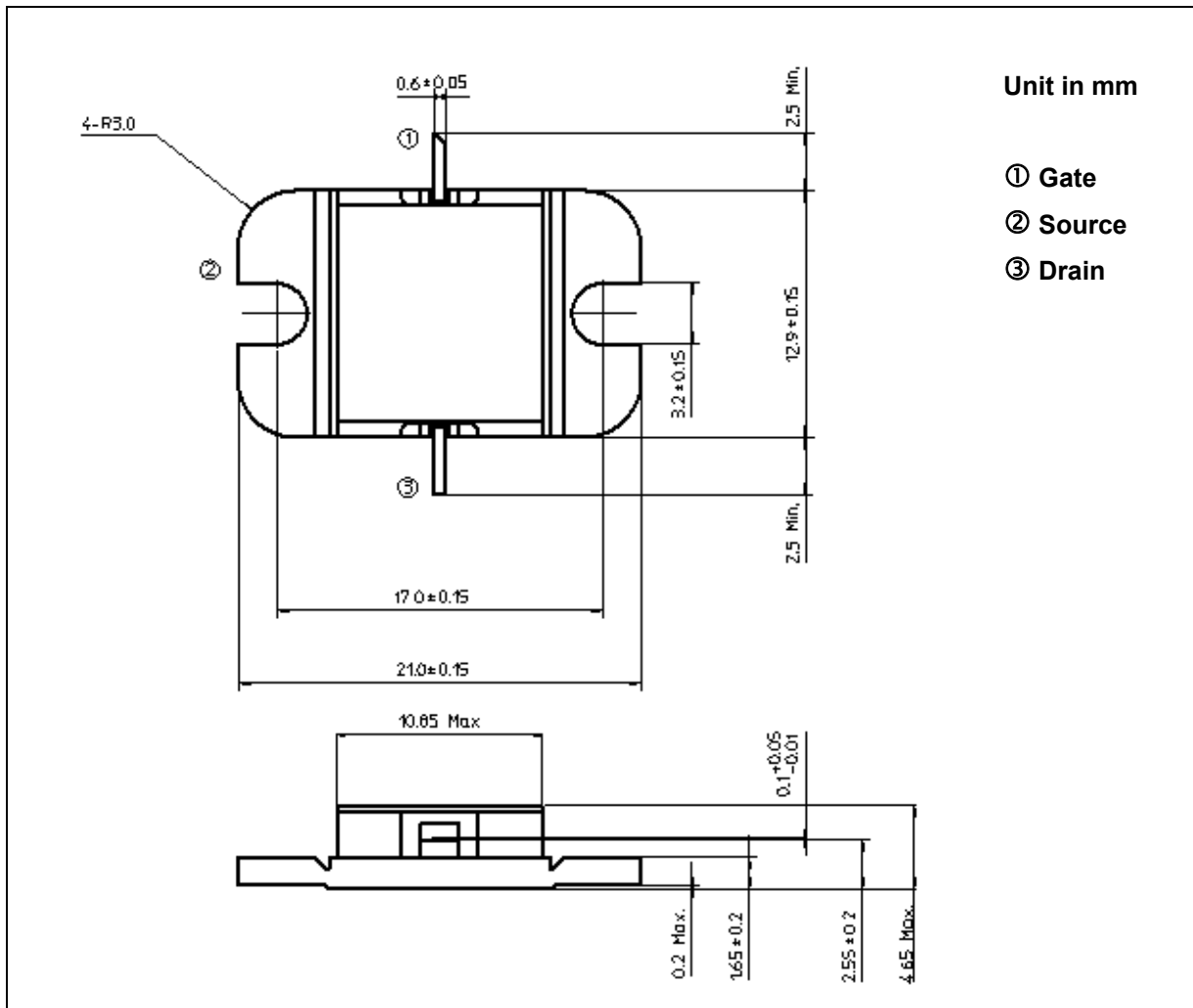
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The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

**ABSOLUTE MAXIMUM RATINGS ( Ta= 25°C )**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	11.5
Total Power Dissipation (Tc= 25 °C)	PT	W	60
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

**PACKAGE OUTLINE (2-11C1B)**

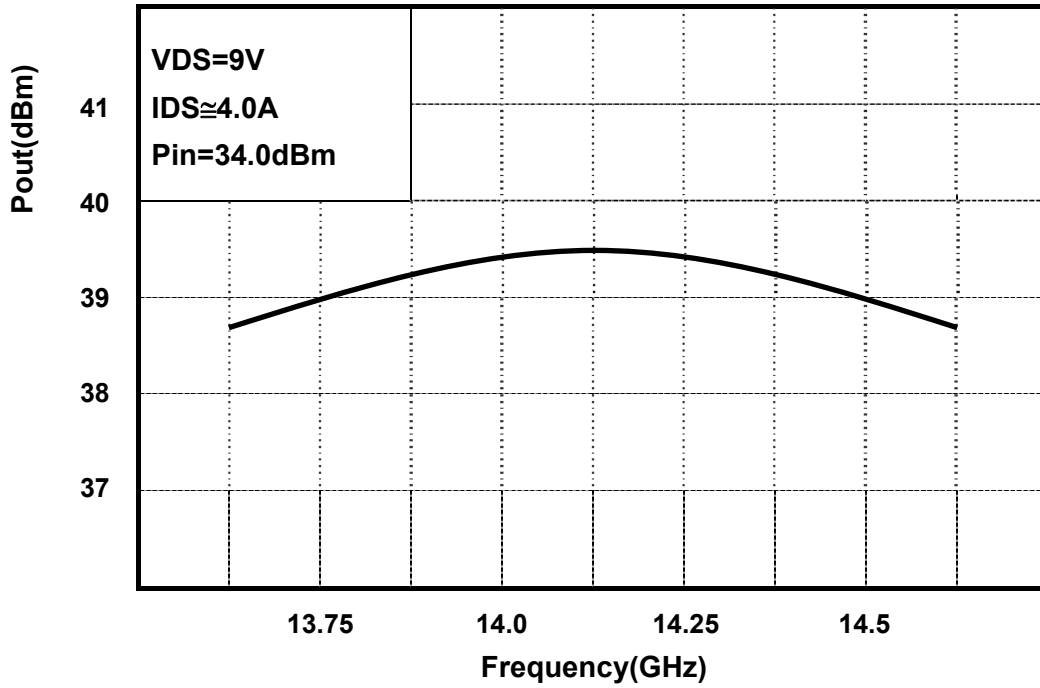


**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

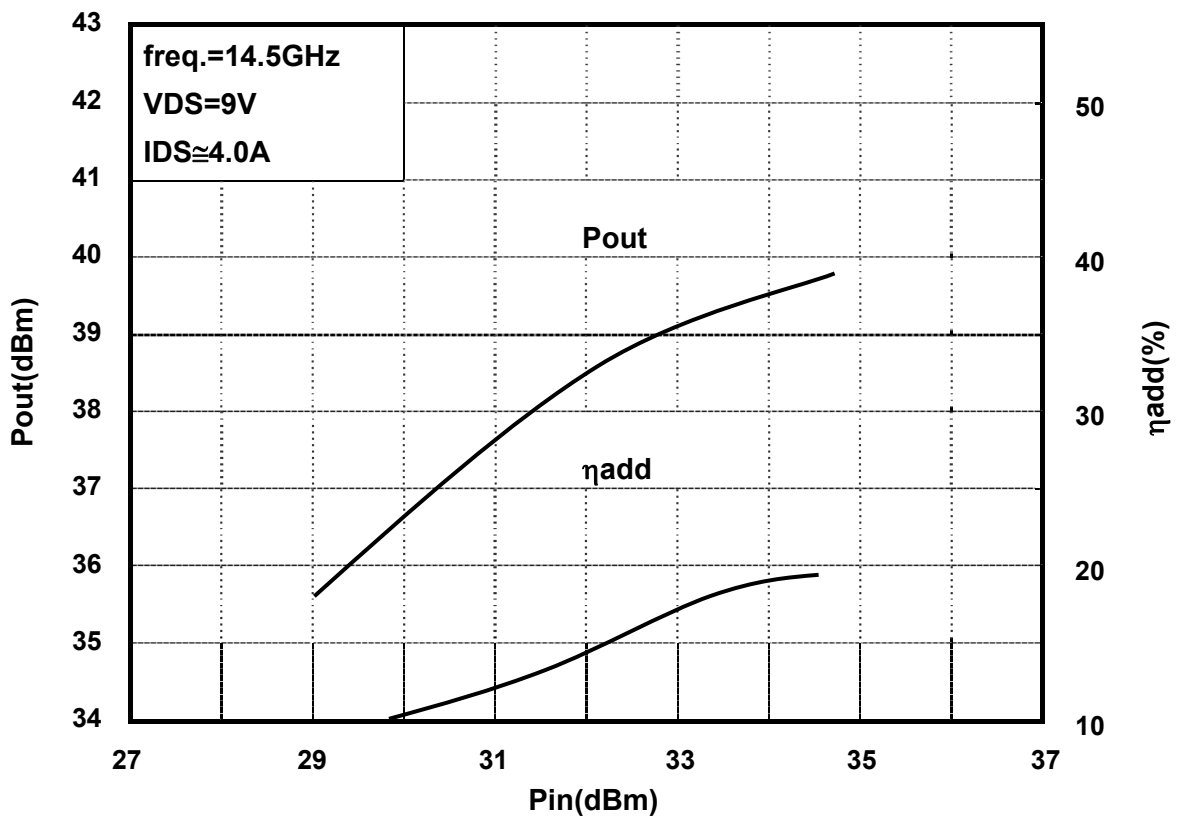
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF PERFORMANCE

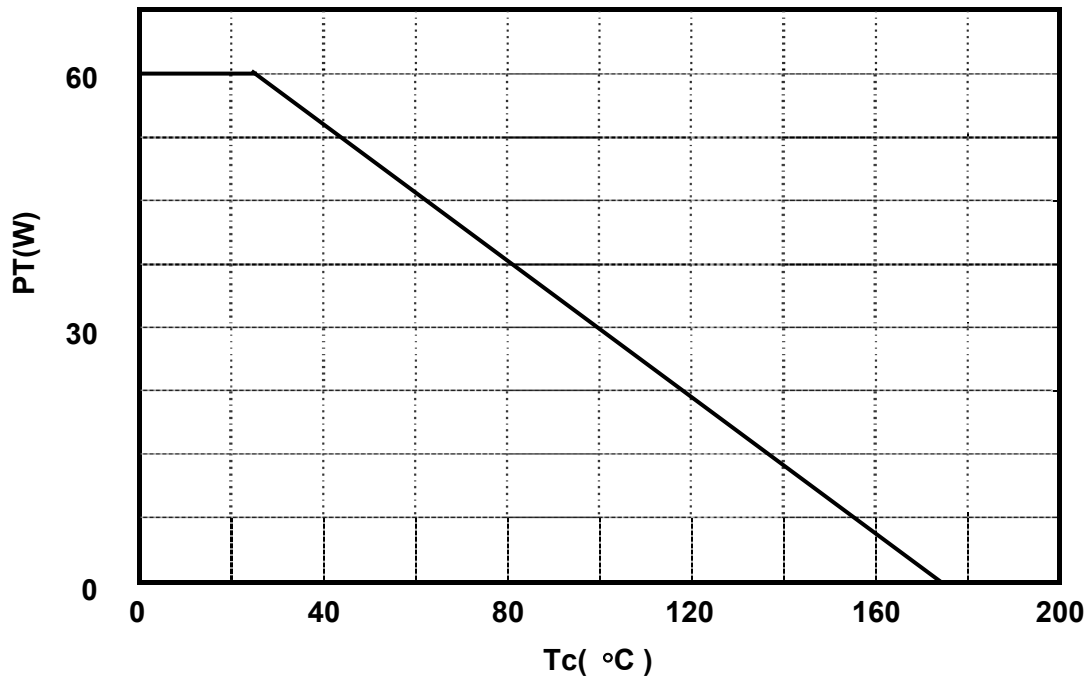
Output Power (Pout) vs. Frequency



Output Power(Pout) vs. Input Power(Pin)



**Power Dissipation(PT) vs. Case Temperature(Tc)**



**IM3 vs. Output Power Characteristics**

